

Specification Sheet

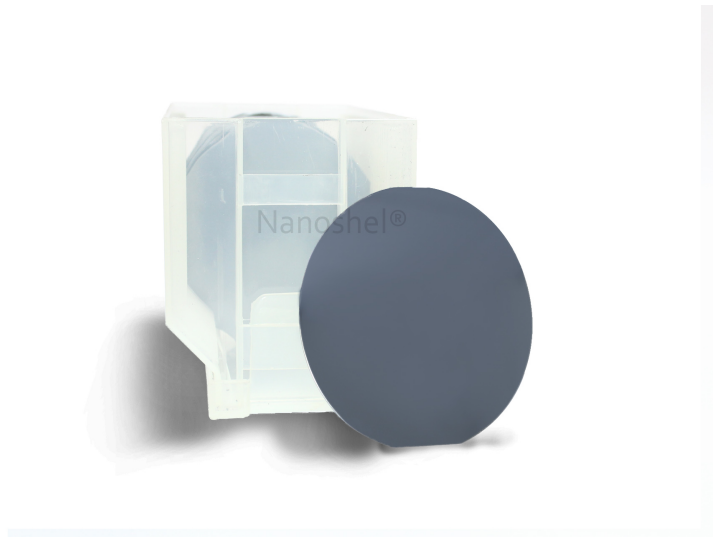
4 inch, Boron Doping

Stock No: NS6130-10-1109, CAS: 7440-21-3

Product	:	Silicon Wafer 4"
Stock No	:	NS6130-10-1109
CAS	:	7440-21-3
Diameter	:	4"
Thickness	:	300±10µm
Dopant	:	Boron
Crystal Orientation	:	< 100>
Type	:	P
Growth Method	:	CZ/FZ
Resistivity	:	1.0-5.0Ω.cm
TTV	:	< 10.0µm
STIR	:	< 2µm
GLOBAL TIR	:	< 5µm
Warp	:	< 50.0µm
LPD	:	< 30 counts @ particles size>0.3µm
Laser Mark	:	None
Edge Profile	:	Rounded
Front Surface	:	Polished
Back Surface	:	Etched
Bow	:	< 50.0µm
Main Inspect Verifier	:	Manager QC

Note: Product Specification are subject to amendment and may change over time

Characterization of 4 inch, Boron Doping



P Type Semiconductor



NANOSHEL
Creating Miracles in Black